

1N3288-1N3297

SILICON POWER DIODE



NAINA

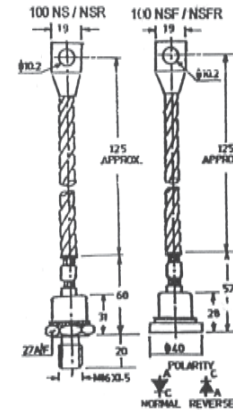
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FEATURES

- Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic

ELECTRICAL SPECIFICATIONS

I_F	Maximum Average Forward Current $T_c=125^\circ\text{C}$	100A
V_{FM}	Maximum peak forward voltage drop @ Rated $I_F(AV)$	1.5V
I_{FSM}	Maximum peak one cycle (non-rep) surge current 10 m sec	2200A
I_{FRM}	Maximum peak repetitive surge current	500 A
I^2t	Maximum I^2t rating (non-rep.) for 5 to 10 msec.	24000 $\text{A}^2 \text{Sec}$



THERMAL MECHANICAL SPECIFICATIONS

θ_{JC}	Maximum thermal resistance Junction to case	0.40°C/W
T_j	Operating Junction Temp.	-65°C to 150°C
T_{stg}	Storage temperature	-65°C to 200°C
	Mounting torque (Non-lubricated threads)	2.0 M-kg min, 3.0 M-kg max
W	Approx, weight	150 gms.

ELECTRICAL RATINGS

TYPE		1N3288	1N3289	1N3290	1N3291	1N3292	1N3293	1N3294	1N3295	1N3296
V_{RRM}	Max. repetitive peak reverse voltage (v)	100	200	300	400	500	600	800	1000	1200
$V_R(RMS)$	Max. R.M.S. reverse voltage(V)	70	140	210	280	350	420	560	700	840
V_R	Max. D.C. Blocking Voltage (V)	100	200	300	400	500	600	800	1000	1200
	Recommended R.M.S. working Voltage(v)	40	80	120	160	200	240	320	400	480
$I_R(AV)$	Max. Average reverse leakage current @ $V_{RRM} T_c 25^\circ\text{C}$ (uA)	200	200	200	200	200	200	200	200	200

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